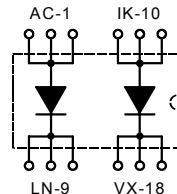


Fast Recovery Epitaxial Diode (FRED)

DSEI 2x101

I_{FAVM} = 2x96 A
V_{RRM} = 600 V
t_{rr} = 35 ns

V _{RSM}	V _{RRM}	Type
V	V	
600	600	DSEI 2x 101-06P



Symbol	Conditions	Maximum Ratings (per diode)		
I _{FRMS}	T _{VJ} = T _{VJM}	150	A	
I _{FAVM} ①	T _C = 70°C; rectangular; d = 0.5	96	A	
I _{FRM}	t _p < 10 µs; rep. rating; pulse width limited by T _{VJM}	tbd	A	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	1200	A	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+150	°C	
P _{tot}	T _C = 25°C	250	W	
V _{ISOL}	50/60 Hz, RMS	2500	V~	
	I _{ISOL} ≤ 1 mA	3000	V~	
M _d	Mounting torque (M4)	1.5 - 2.0	Nm	
		14 - 18	lb.in.	
Weight		24	g	

Symbol	Conditions	Characteristic Values (per diode)		
		typ.	max.	
I _R	T _{VJ} = 25°C V _R = V _{RRM}	3	mA	
	T _{VJ} = 25°C V _R = 0.8 • V _{RRM}	1	mA	
	T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	20	mA	
V _F	I _F = 100 A; T _{VJ} = 150°C	1.17	V	
	T _{VJ} = 25°C	1.25	V	
V _{T0}	For power-loss calculations only	0.7	V	
r _T	T _{VJ} = T _{VJM}	4.7	mΩ	
R _{thJC}		0.5	K/W	
R _{thCK}		0.05	K/W	
t _{rr}	I _F = 1 A; -di/dt = 400 A/µs	40	60	ns
	V _R = 30 V; T _{VJ} = 25°C			
I _{RM}	V _R = 100 V; I _F = 80 A; -di _F /dt = 200 A/µs	19	24	A
	L ≤ 0.05 µH; T _{VJ} = 100°C			
d _s	Creeping distance on surface	min. 11.2	mm	
d _a	Creeping distance in air	min. 11.2	mm	
a	Allowable acceleration	max. 50	m/s ²	

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 V_{RRM}, duty cycle d = 0.5
Data according to IEC 60747

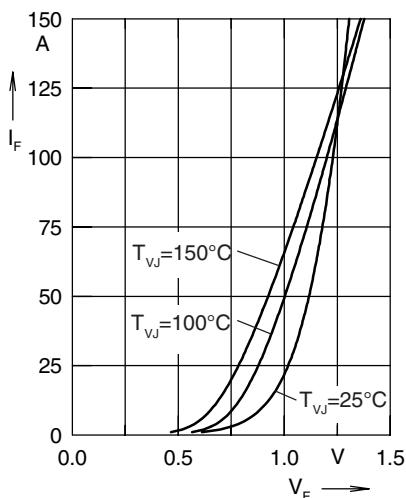
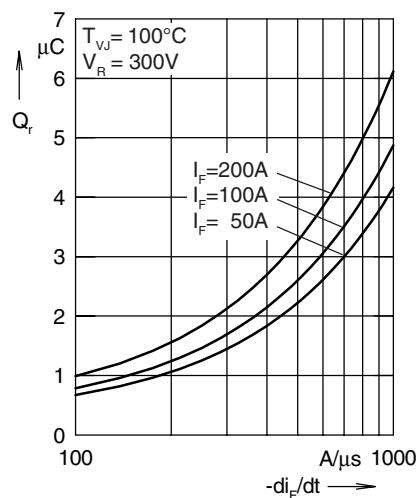
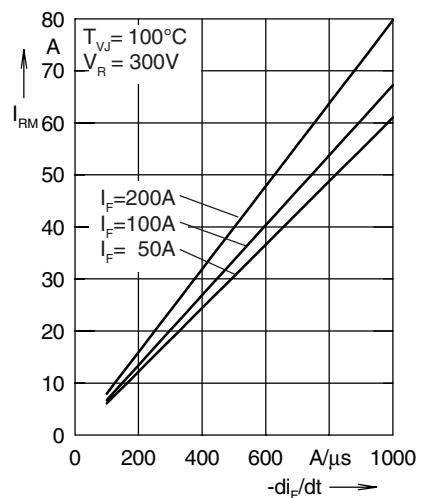
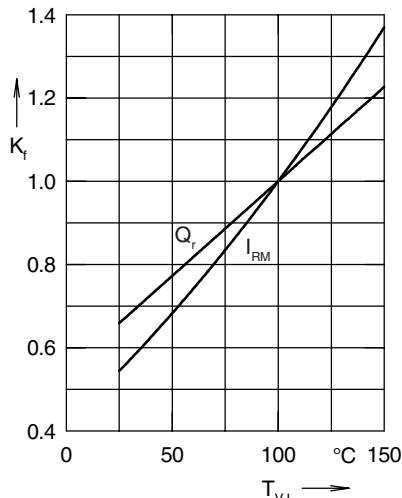
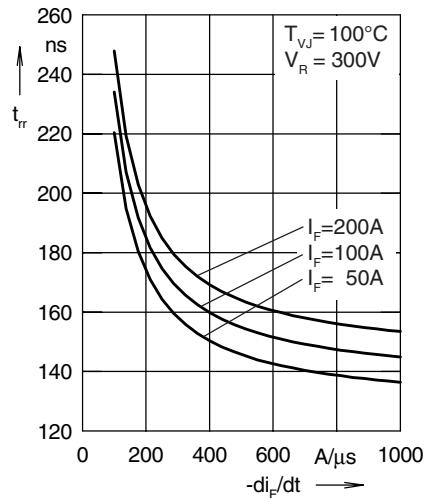
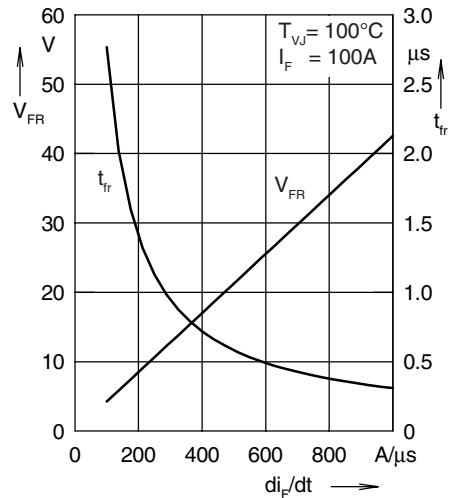
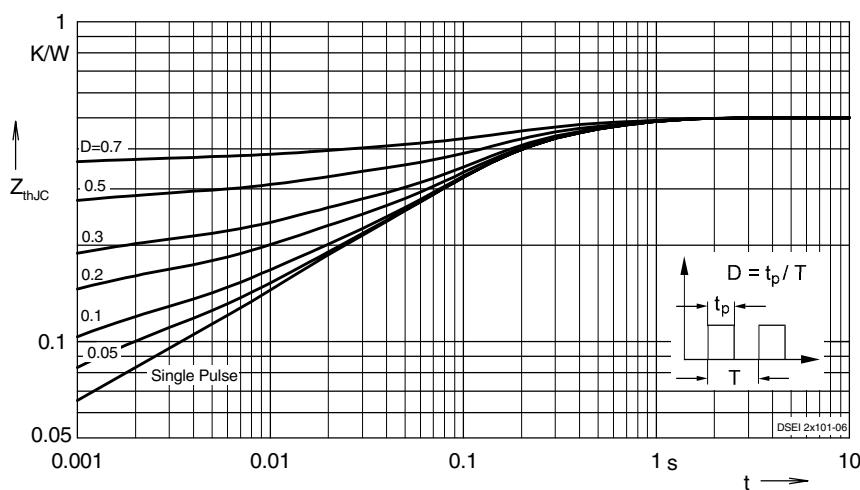
Fig. 1 Forward current I_F versus V_F Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$ Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$ Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ} Fig. 5 Recovery time t_{rr} versus $-di_F/dt$ Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt 

Fig. 7 Transient thermal impedance junction to case at various duty cycles

Dimensions in mm (1mm = 0.0394")

